Silicon NPN Epitaxial

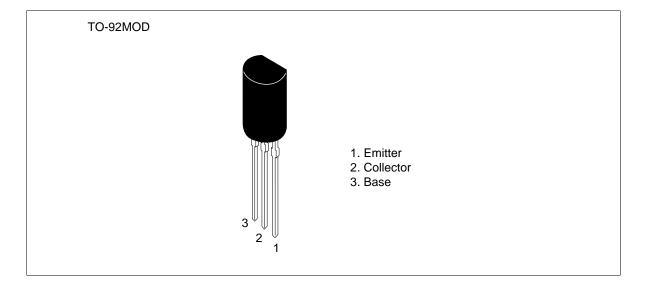
HITACHI

ADE-208-1137 (Z) 1st. Edition Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SB647/A

Outline





Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SD667	2SD667A	Unit
Collector to base voltage	V_{CBO}	120	120	V
Collector to emitter voltage	V _{CEO}	80	100	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	1	1	А
Collector peak current	i _{C(peak)}	2	2	А
Collector power dissipation	P _c	0.9	0.9	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-50 to +150	°C

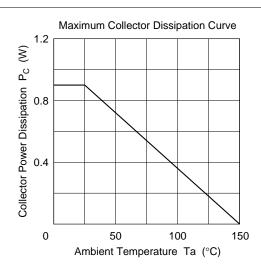
Electrical Characteristics ($Ta = 25^{\circ}C$)

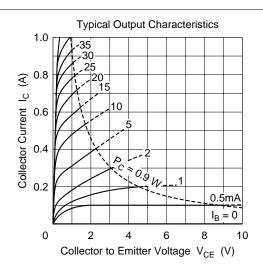
		2SD6	67		2SD667A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	_	_	120	_	_	V	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	_	_	100	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	10	_	_	10	μΑ	$V_{CB} = 100 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE1} *1	60	_	320	60	_	200		$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA}^{*2}$
	h _{FE2}	30	_	_	30	_	_		$V_{CE} = 5 \text{ V},$ $I_{C} = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1	_	_	1	V	$I_{\rm C} = 500 \text{ mA},$ $I_{\rm B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	_	_	1.5	_	_	1.5	V	$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA}^{*2}$
Gain bandwidth product	f _T	_	140	_		140		MHz	$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA}^{*2}$
Collector output capacitance	Cob	_	12	_	_	12	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz

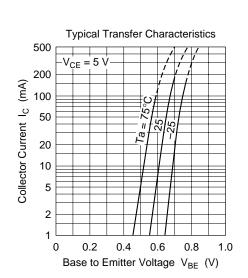
Notes: 1. The 2SD667 and 2SD667A are grouped by h_{FE1} as follows.

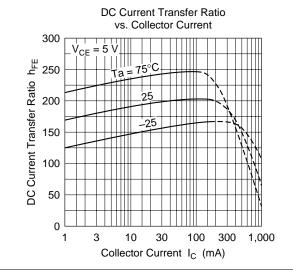
2. Pulse test

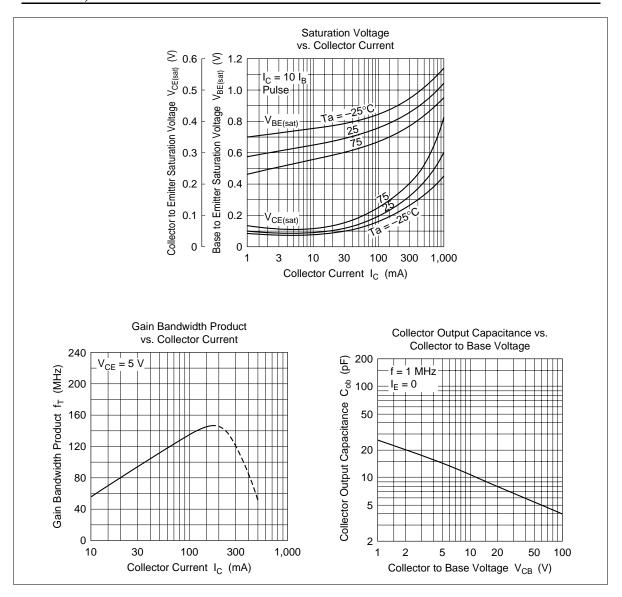
	В	С	D
2SD667	60 to 120	100 to 200	160 to 320
2SD667A	60 to 120	100 to 200	



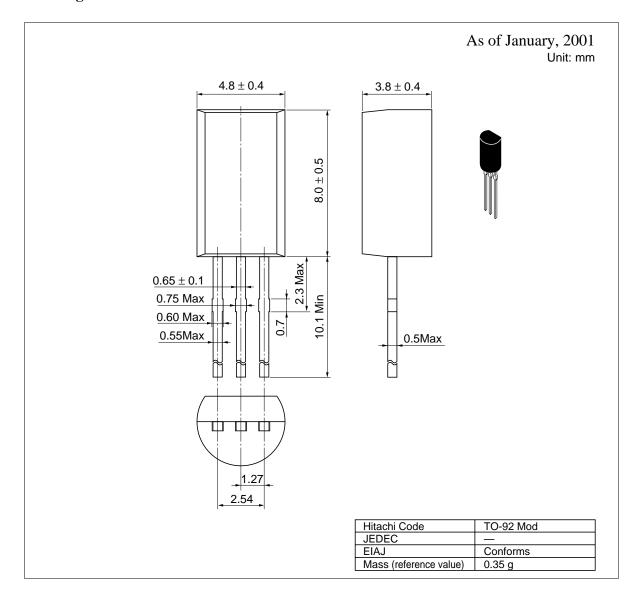








Package Dimensions



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